CERTIFICATE OF Tapplicant(s): KAMALES	RANSMISSION BY FA II K. SRIVASTAVA ET AL.	CSIMILE (37 CFR 1.8)	Docket No. FIS920030359US1
Application No. 10/708,649	Filing Date 05/17/2004	Examiner THERESA T. DOAN	Group Art Unit 2814
nvention: METHOD FO FFECTS OF SEED LAYE	R FORMING ROBUST SOL R	DER INTERCONNECT STRUCTIO	RES BY REDUCING
			RECEIVED
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hereby certify that this being facsimile transmitt		esponse to Restriction Requirement	
05/12/2005			703-872-9306
		Jessica L. Husto (Typed or Printed Name of Person Signature) Jessica L. Husto (Signature)	aing Certificate)
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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

APPLICANT:	KAMALESH K. SRIVASTAVA ET AL.	Group Art Unit: 2814
SERIAL NUMBER:	10/708,649) Examiner:
HILLID:	May 17, 2004) Theresa T. Doan
FOR;	METHOD FOR FORMING ROBUST SOLDER INTERCONNECT STRUCTURES BY REDUCING EFFECTS OF SEED LAYER	Confirmation No. 2648)

Commissioner For Patents P.O. Box 1450 Alexandria, VA. 22313-1450

RESPONSE TO RESTRICTION REQUIREMENT

In response to the restriction requirement mailed on May 2, 2005, and in accordance with the provisions under 37 CFR § 1.115 and 1.143, the Applicants submit the following election for further prosecution on the merits:

Election:

Applicants hereby elect, without traverse, Group II, claims 6-20, a method for forming an interconnect structure comprising annealing the semiconductor device as to cause atoms from the barrier layer to diffuse into the seed layer there underneath, wherein the annealing causes diffused regions of the seed layer to have an altered electrical resistivity and electrode potential with respect to undiffused regions of the seed layer.